

HF/VHF power transistor

BLW83

Description:

N-P-N silicon planar epitaxial transistor for use in transmitting amplifiers operating in the HF and VHF bands, with a nominal supply voltage of 28 V. The transistor is specified for s.s.b. applications as linear amplifier in class-A and AB. The device is resistance stabilized and is guaranteed to withstand severe load mismatch conditions. Matched hFE groups are available on request.

Features:

It has a 3/8" flange envelope with a ceramic cap. All leads are isolated from the flange.

Data:

MODE OF OPERATION	V _{CE} V	f MHz	P _L W	G _p dB	η _{dt} %	I _C A	d ₃ dB	T _h °C
s.s.b. (class-A)	26	1,6 – 28	0 – 10 (P.E.P.)	> 20	–	1,35	< –40	70
s.s.b. (class-AB)	28	1,6 – 28	3 – 30 (P.E.P.)	typ. 21	typ. 40	typ. 1,34	typ. –30	25

Drawings:

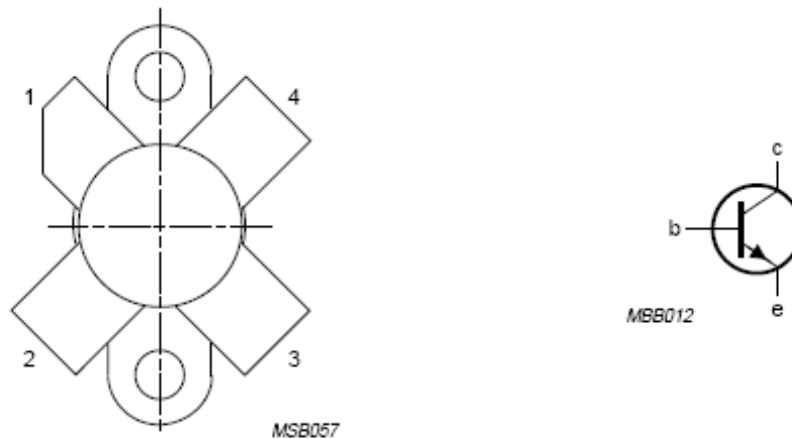
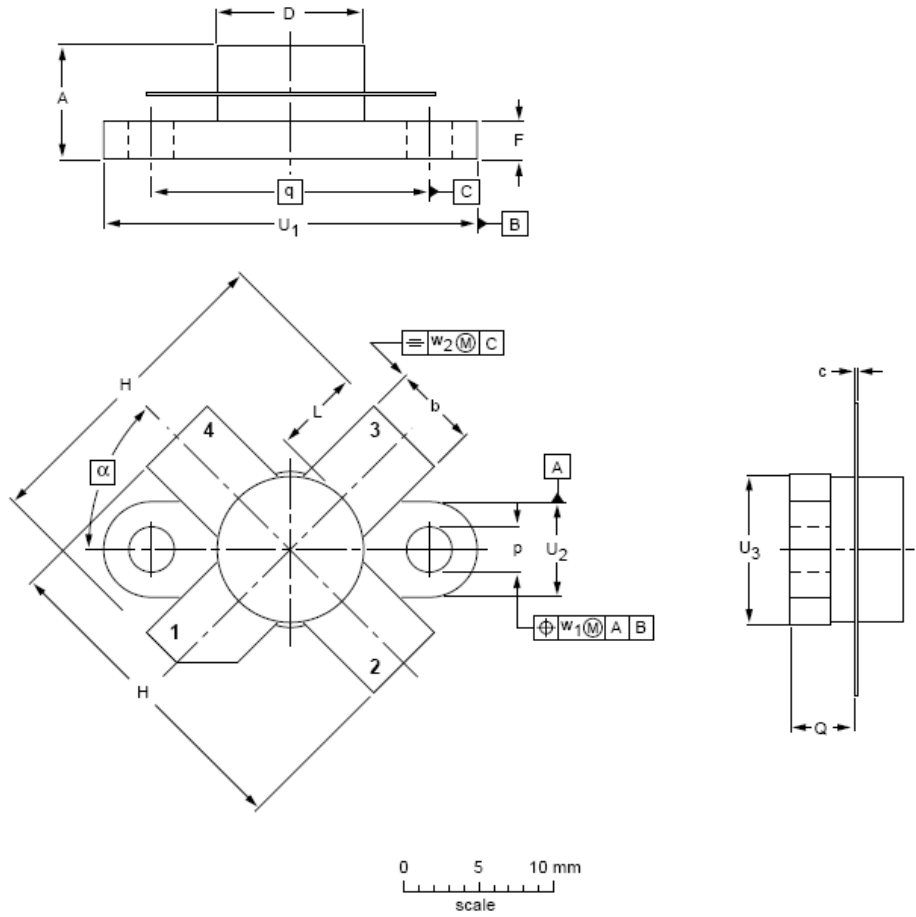


Fig.1 Simplified outline and symbol.

PINNING - SOT123

PIN	DESCRIPTION
1	collector
2	emitter
3	base
4	emitter



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

UNIT	A	b	c	D	D ₁	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.47 6.37	5.82 5.56	0.18 0.10	9.73 9.47	9.63 9.42	2.72 2.31	20.71 19.93	5.61 5.16	3.33 3.04	4.63 4.11	18.42	25.15 24.38	6.61 6.09	9.78 9.39	0.51	1.02	45°
inches	0.294 0.251	0.229 0.219	0.007 0.004	0.383 0.373	0.397 0.371	0.107 0.091	0.815 0.785	0.221 0.203	0.131 0.120	0.182 0.162	0.725	0.99 0.96	0.26 0.24	0.385 0.370	0.02	0.04	